

*FIG. 1*

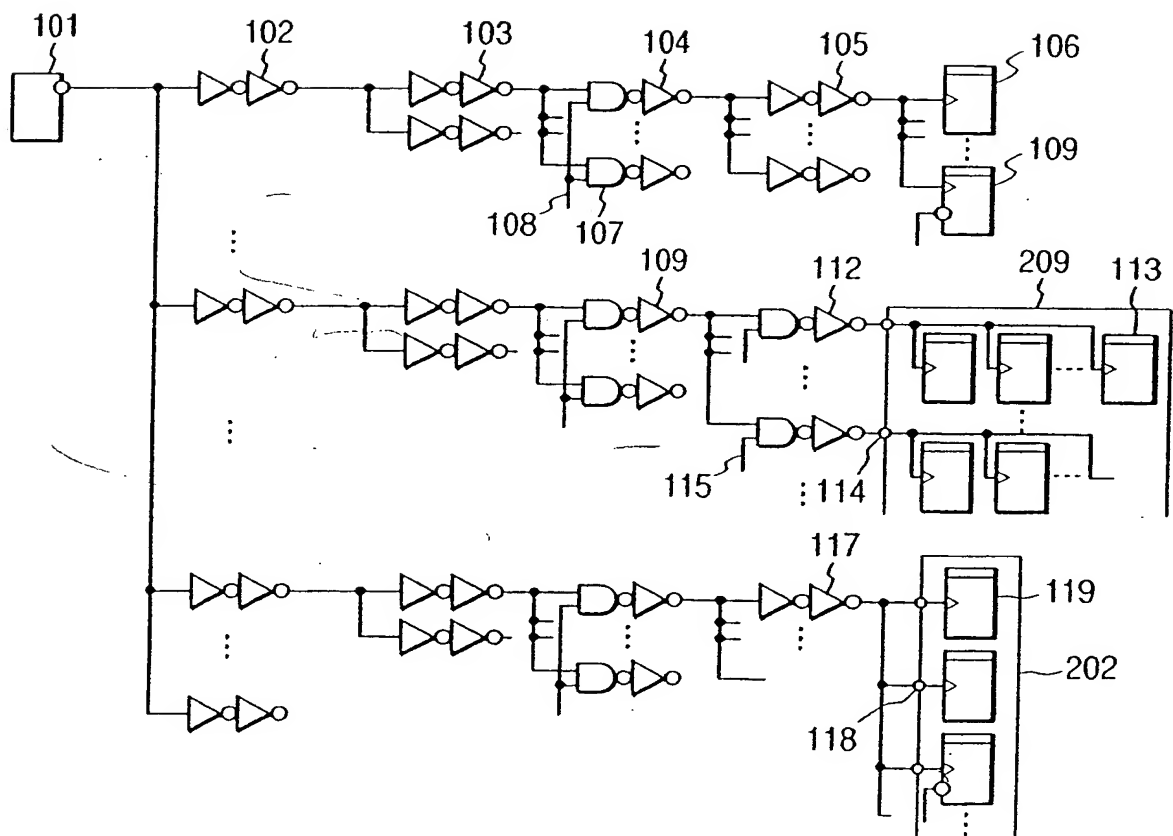
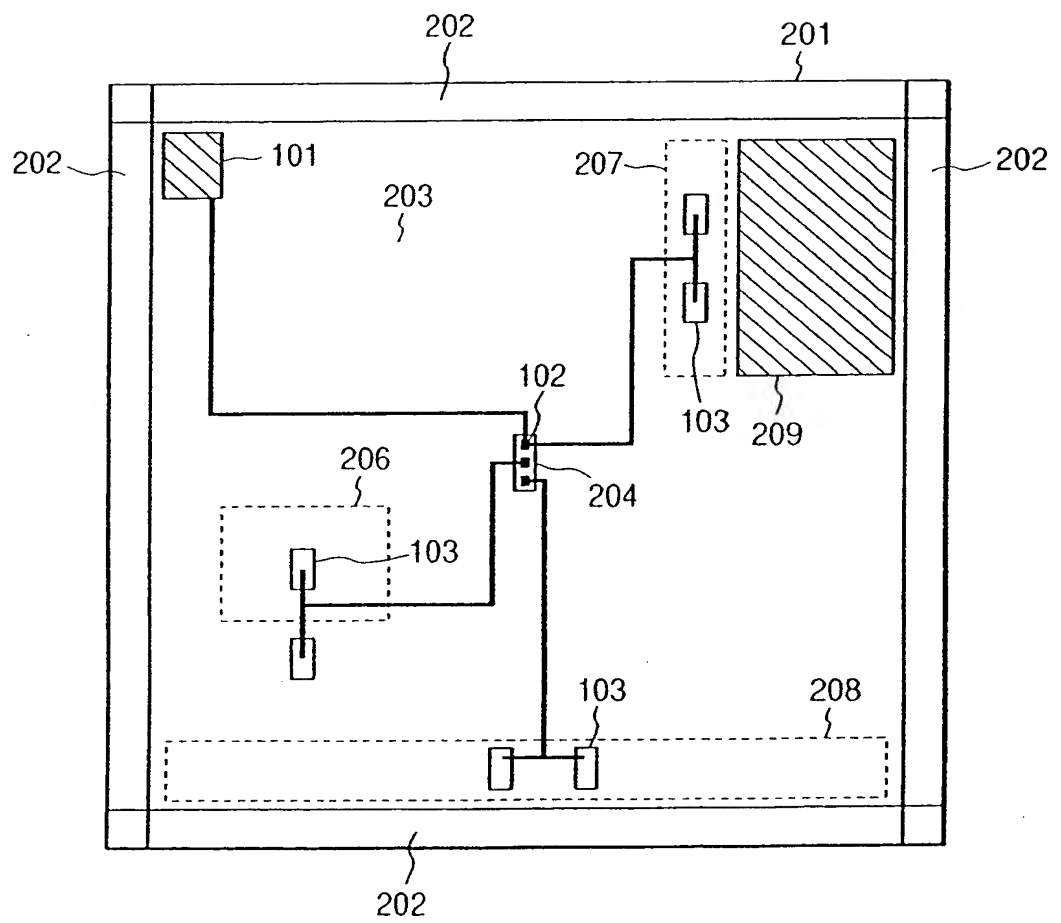


FIG. 2



This cross-sectional view shows a central channel region 302, which is a thin layer of semiconductor material. It is flanked by gate regions 303, which are thicker layers of semiconductor material. The gate regions 303 are separated by source/drain regions 301. A gate stack 304/305 is formed on top of the gate regions 303, with the gate stack 304 being the top layer and the gate stack 305 being the bottom layer. The source/drain regions 301 are also covered by the gate stack 304/305.

FIG. 5

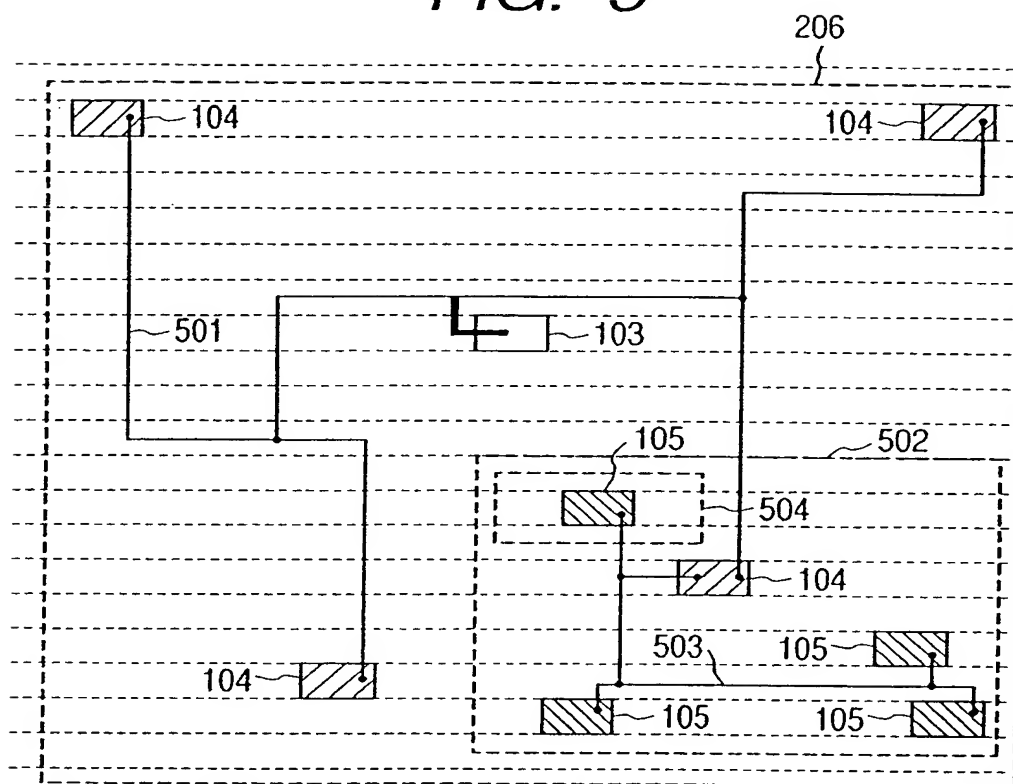


FIG. 6

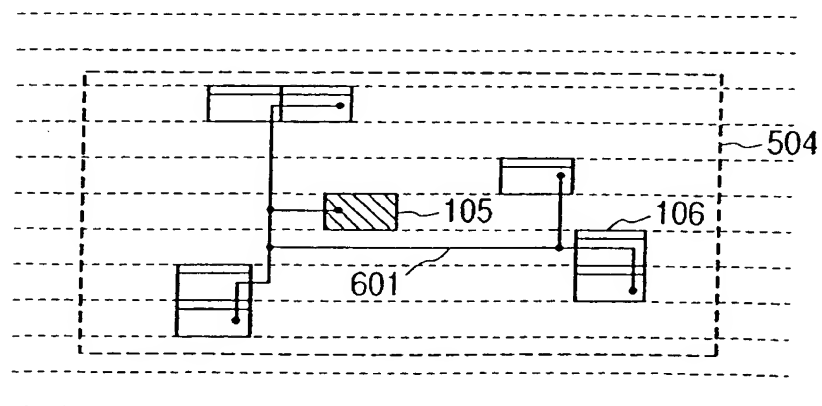


FIG. 7

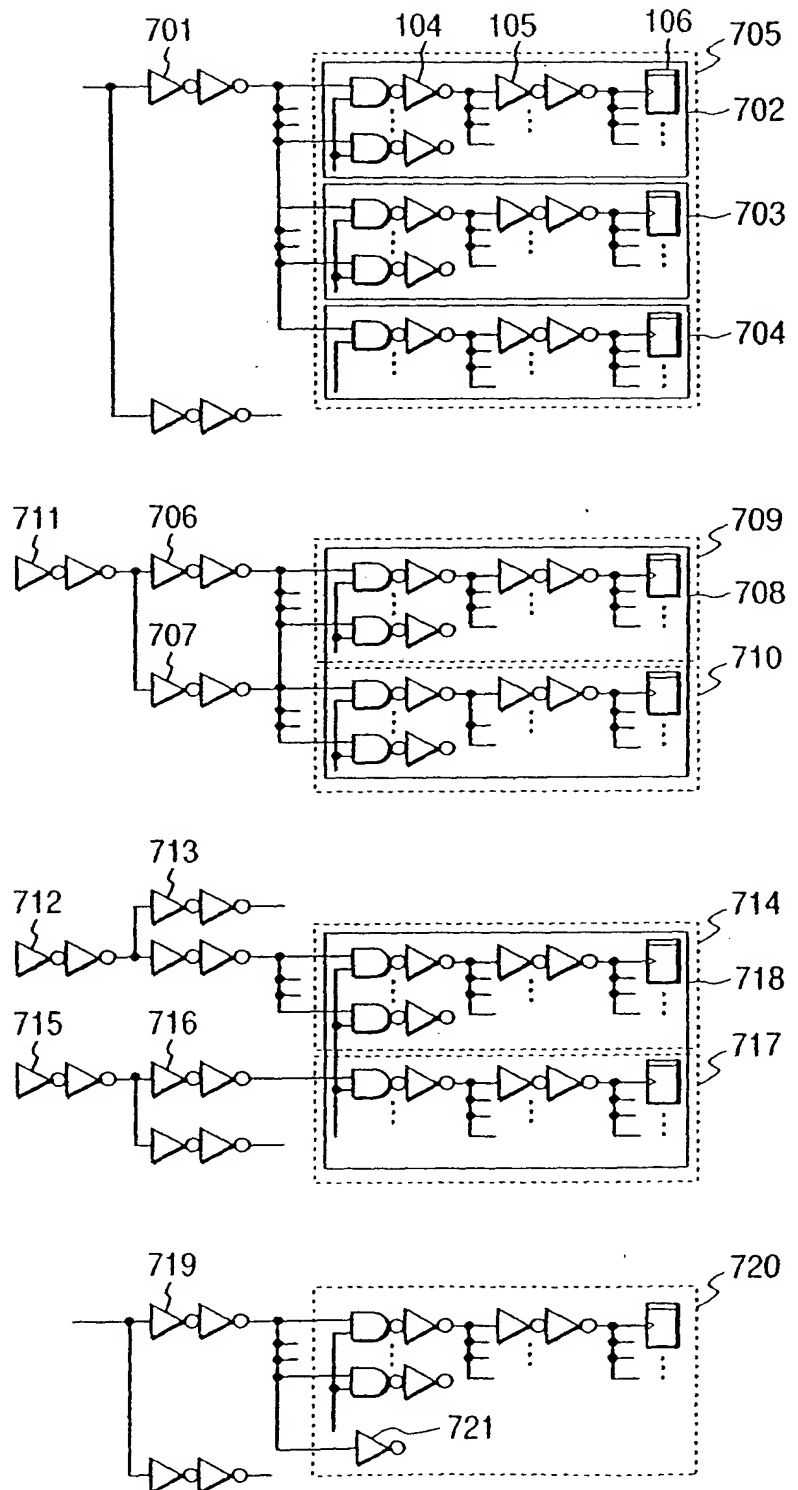


FIG. 8

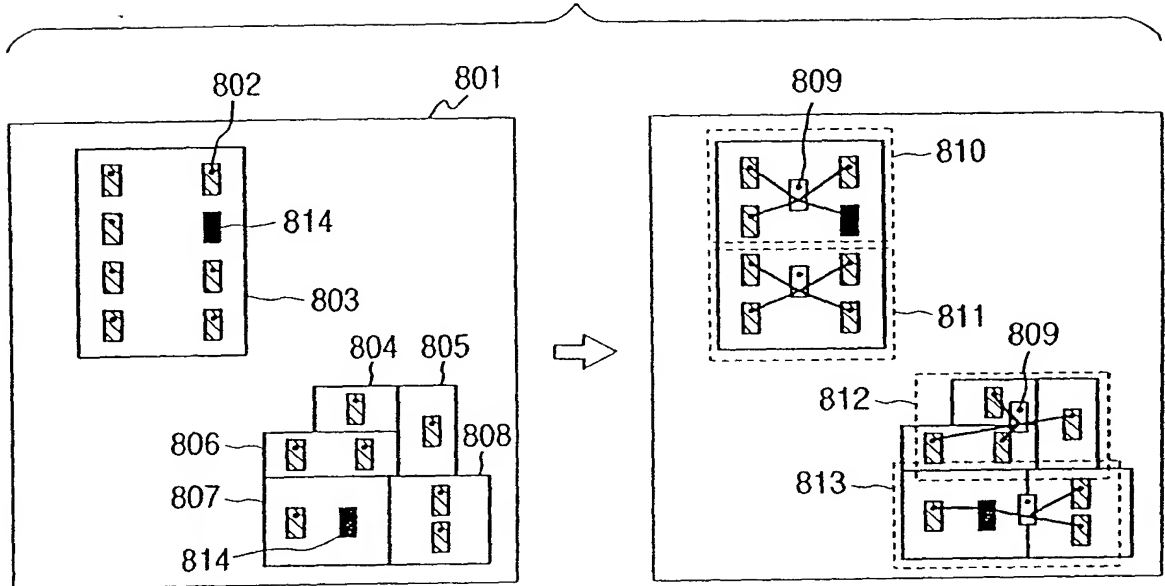


FIG. 9

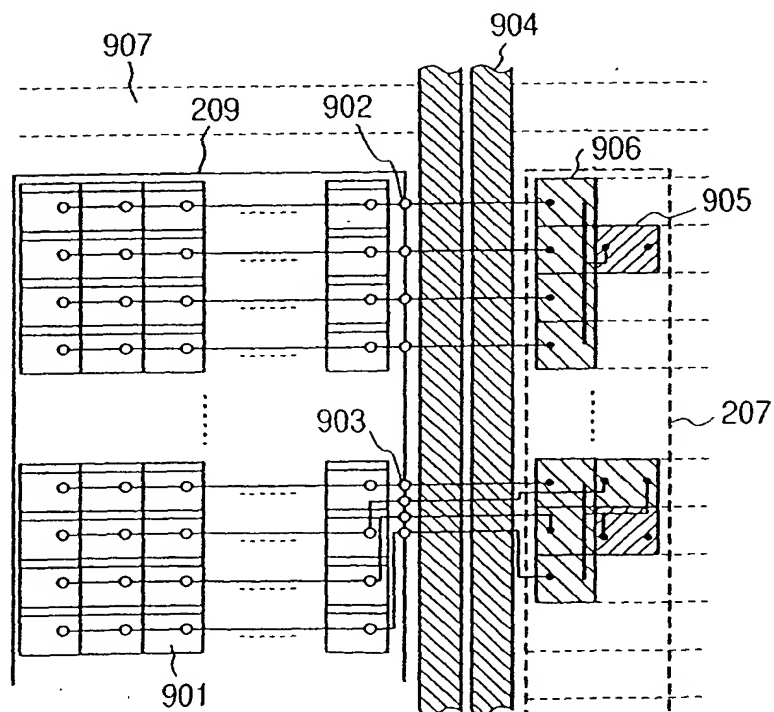


FIG. 10

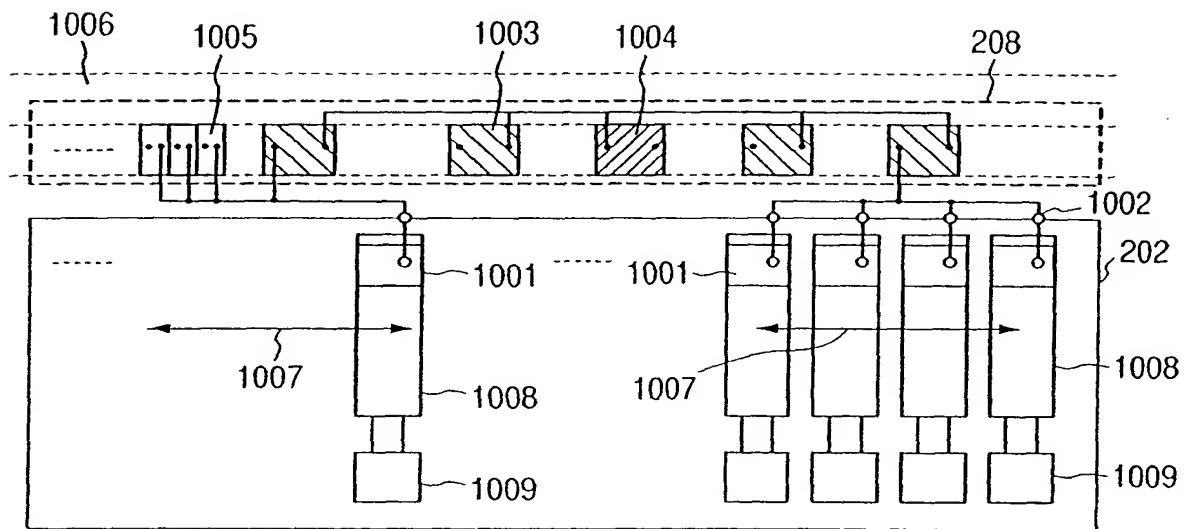


FIG. 11

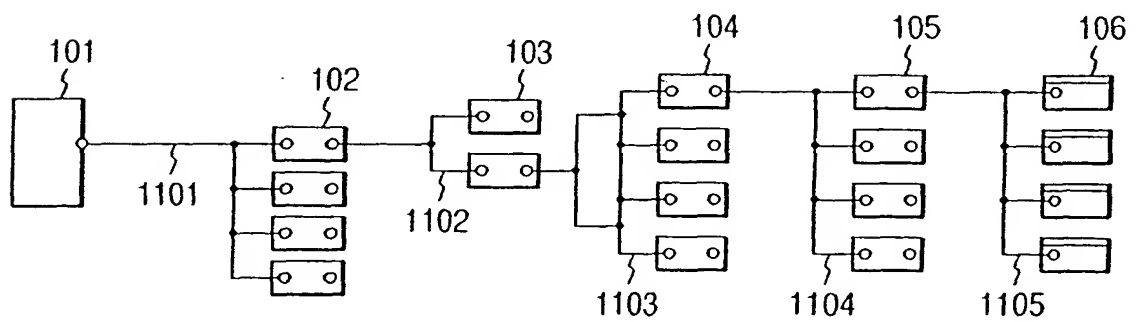


FIG. 12

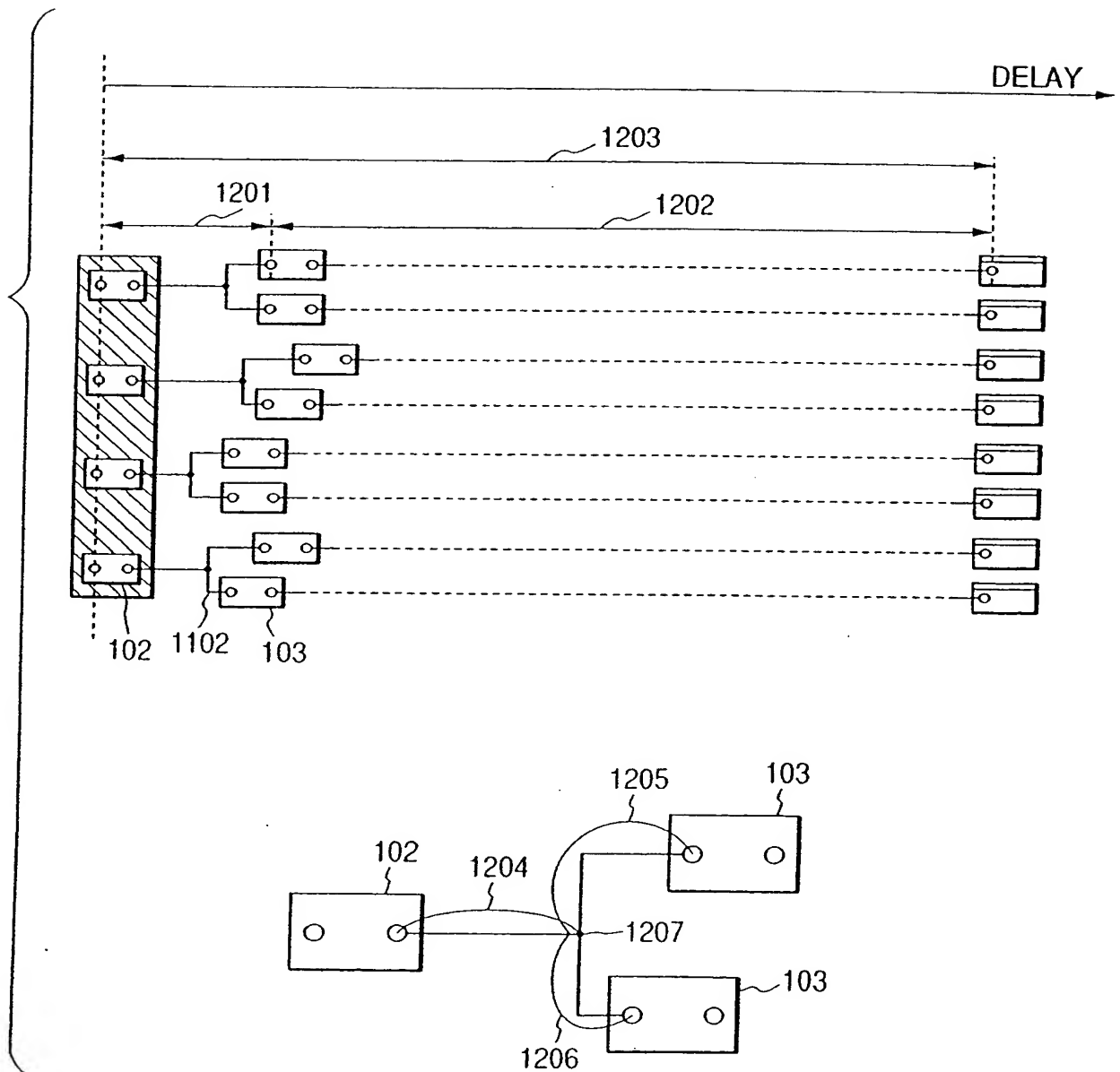




FIG. 13

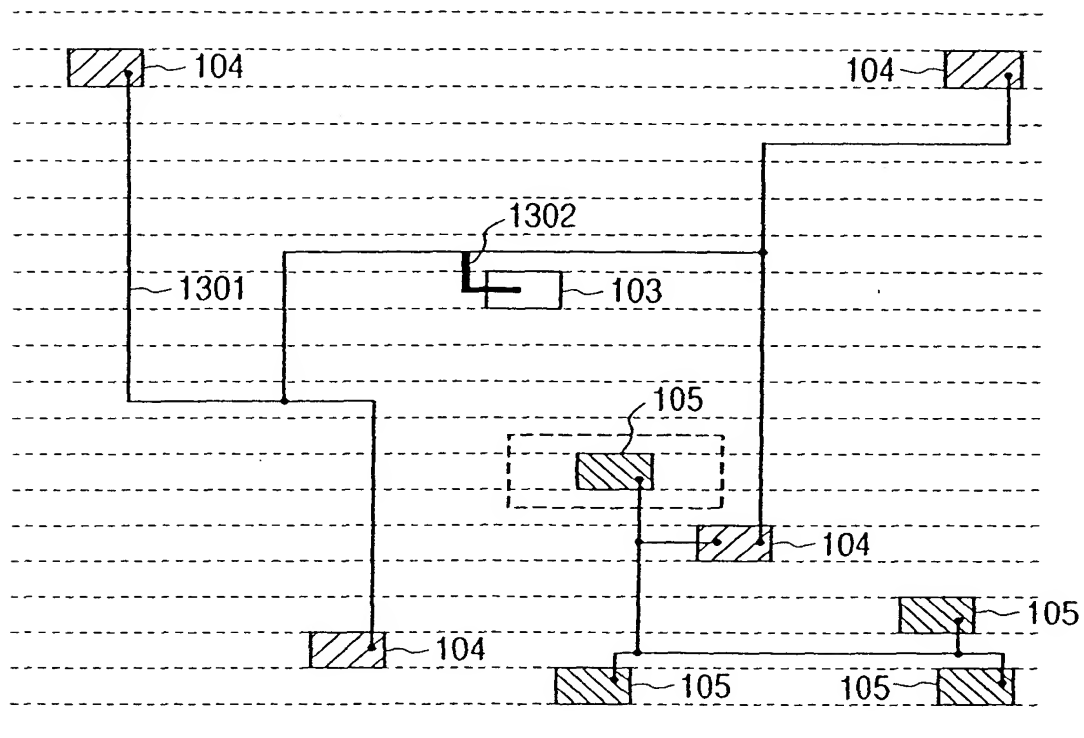


FIG. 14

